

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOS π)

TK15A50D

Switching Regulator Applications

- Low drain-source ON-resistance: $R_{DS(ON)} = 0.24 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 7.0 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 10 \mu\text{A}$ ($V_{DS} = 500 \text{ V}$)
- Enhancement mode: $V_{th} = 2.0$ to 4.0 V ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	500	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	15	A
	Pulse ($t = 1 \text{ ms}$) (Note 1)	I_{DP}	60	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	50	W
Single pulse avalanche energy (Note 2)		E_{AS}	542	mJ
Avalanche current		I_{AR}	15	A
Repetitive avalanche energy (Note 3)		E_{AR}	5.0	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	2.5	$^\circ\text{C/W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ\text{C/W}$

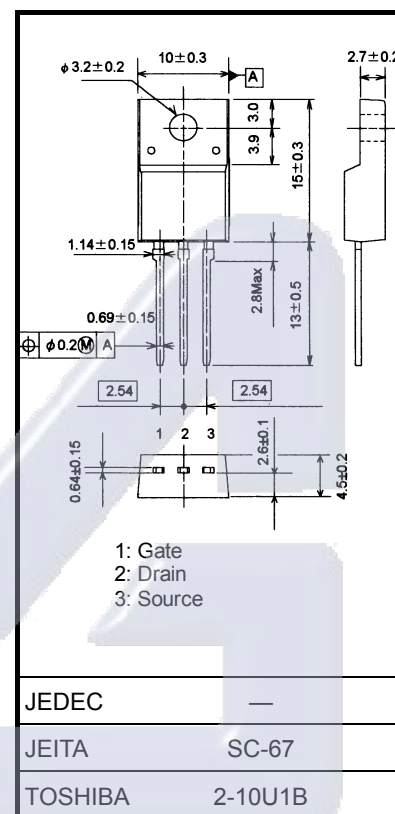
Note 1: Ensure that the channel temperature does not exceed 150°C .

Note 2: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 4.1 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = 15 \text{ A}$

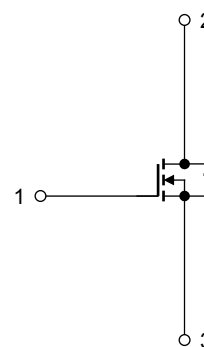
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

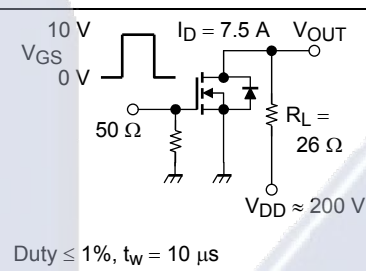
Unit: mm



Weight : 1.7 g (typ.)

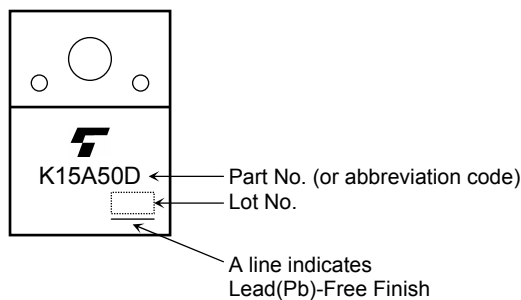


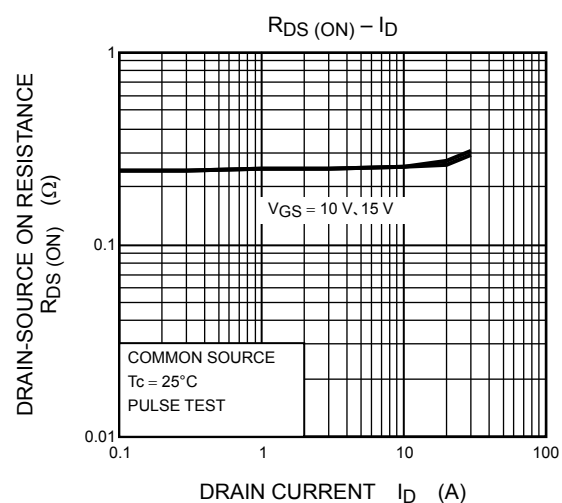
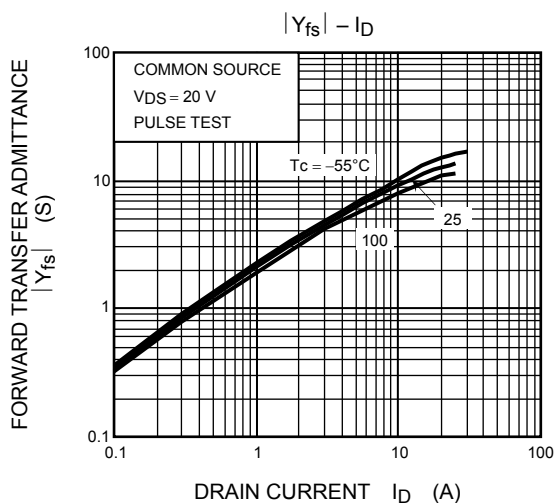
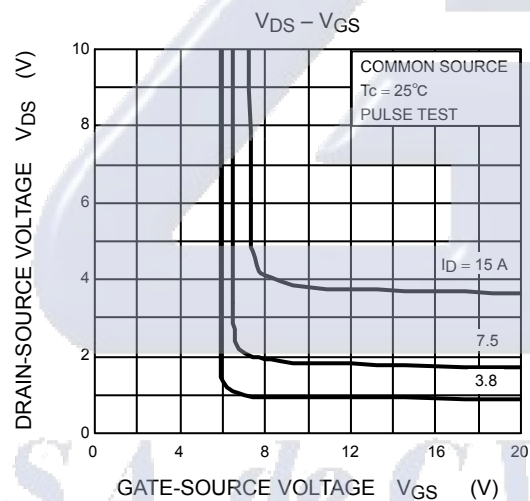
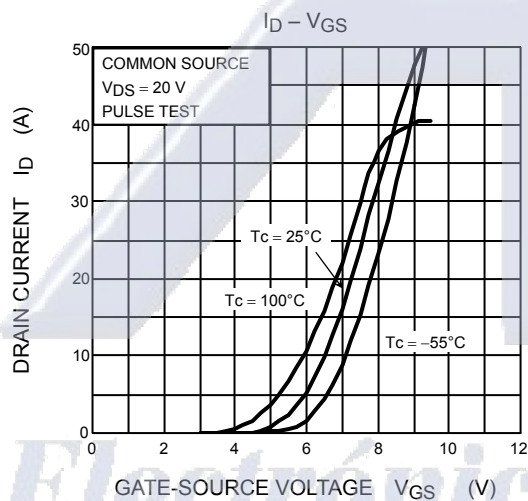
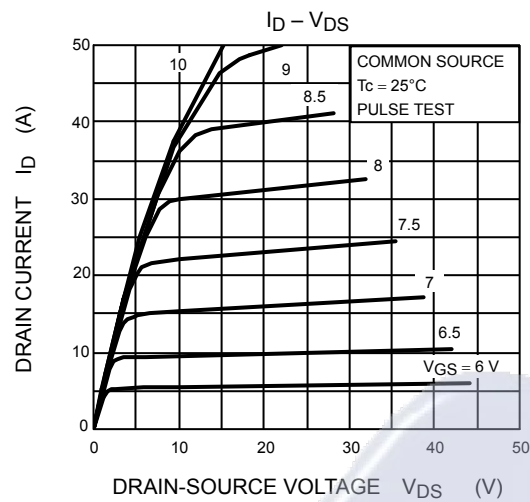
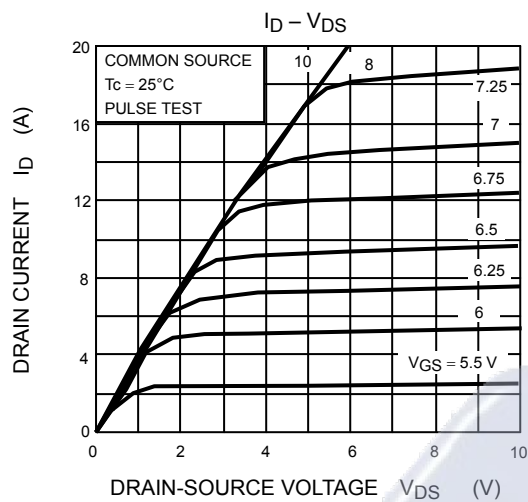
TOSHIBA**TK15A50D****Electrical Characteristics (Ta = 25°C)**

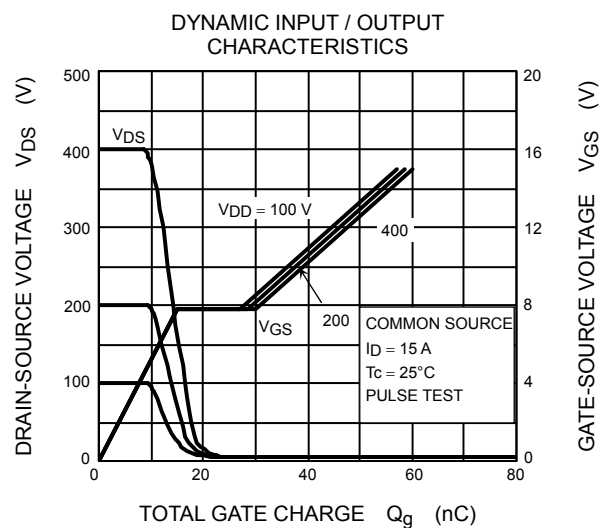
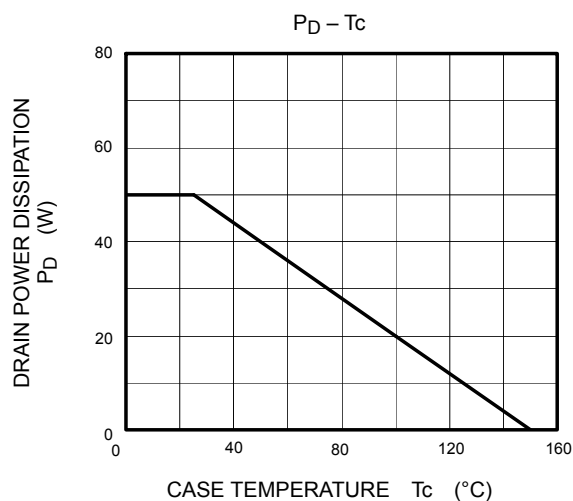
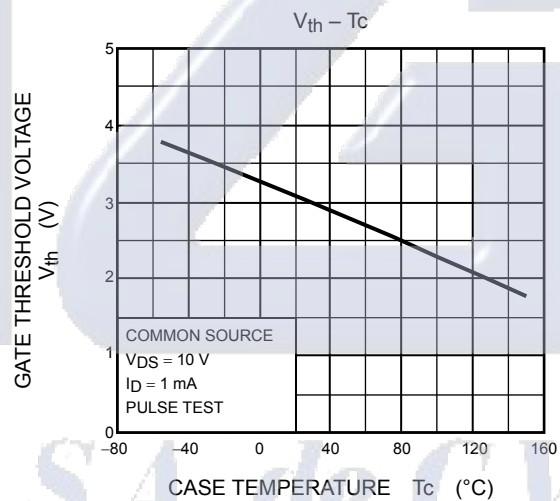
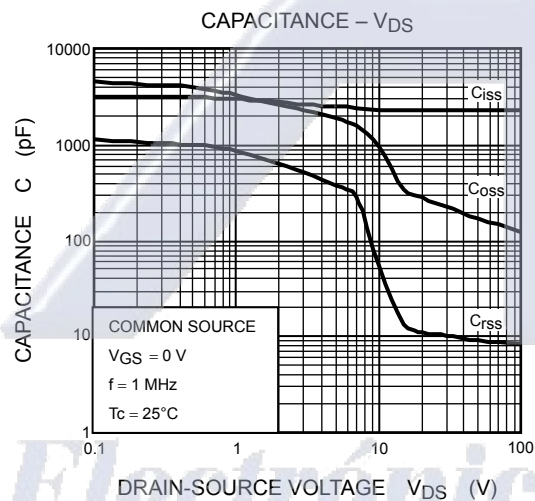
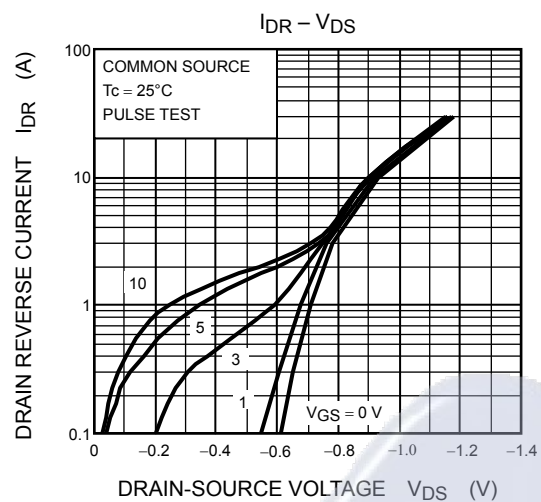
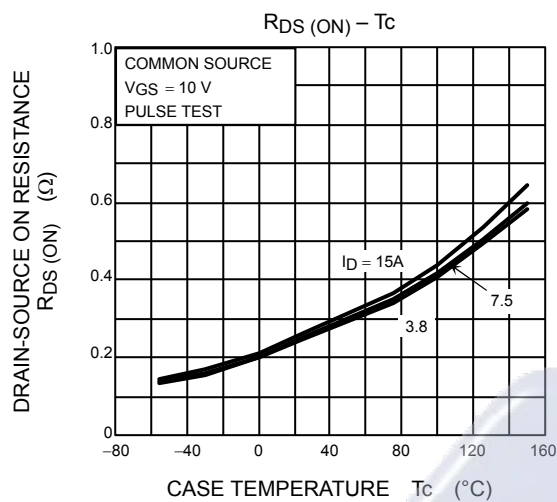
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 1	μA
Drain cut-off current		I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	500	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	V
Drain-source ON-resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 7.5\text{ A}$	—	0.24	0.3	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 7.5\text{ A}$	2.0	7.0	—	S
Input capacitance		C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	2300	—	pF
Reverse transfer capacitance		C_{rss}		—	10	—	
Output capacitance		C_{oss}		—	250	—	
Switching time	Rise time	t_r		—	50	—	ns
	Turn-on time	t_{on}		—	100	—	
	Fall time	t_f		—	25	—	
	Turn-off time	t_{off}		—	140	—	
Total gate charge		Q_g	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	—	40	—	nC
Gate-source charge		Q_{gs}		—	25	—	
Gate-drain charge		Q_{gd}		—	15	—	

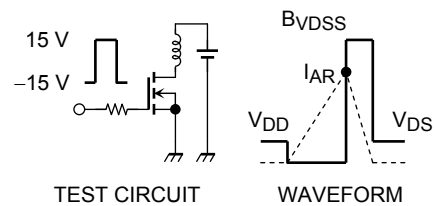
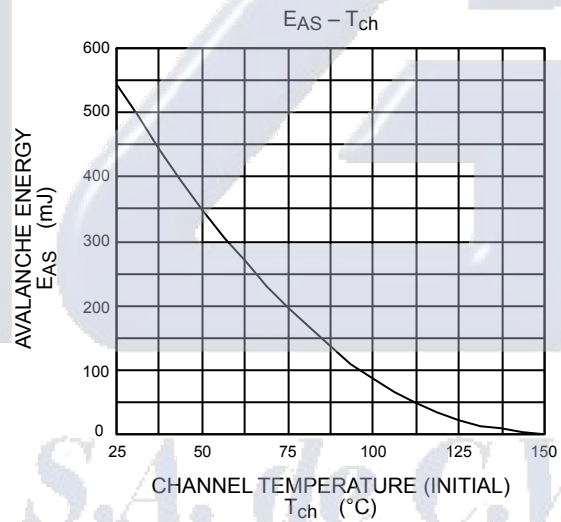
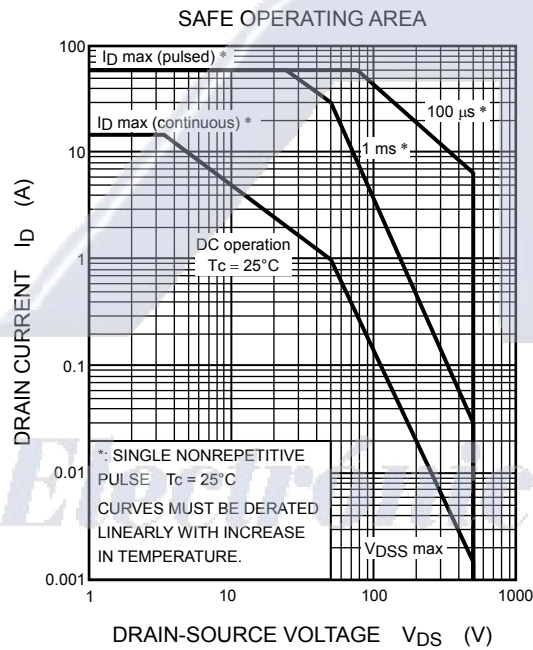
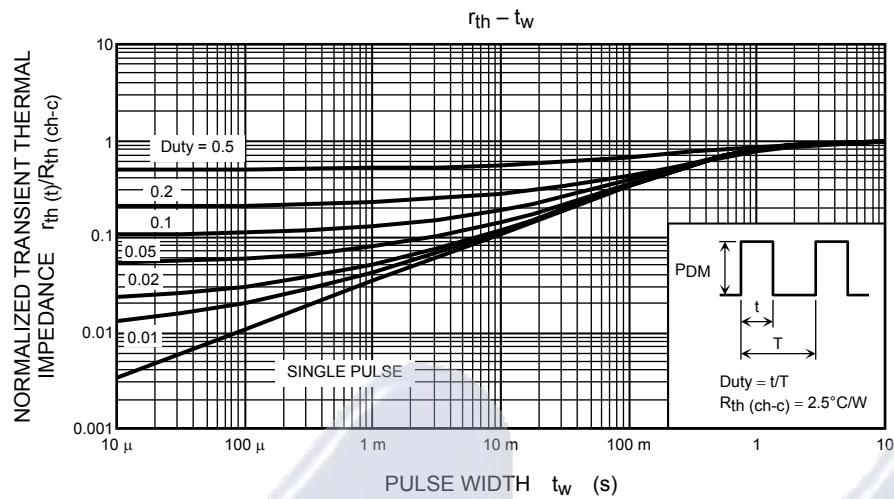
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	15	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	60	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 15\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 15\text{ A}, V_{GS} = 0\text{ V},$	—	1600	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	20	—	μC

Marking



TOSHIBA**TK15A50D**



$$R_G = 25 \, \Omega$$

$$V_{DD} = 90 \, V, L = 4.1 \, mH$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$